



MEGAPOSIT™ SPR™ 220 SERIES PHOTORESISTS

For i-Line Applications

DESCRIPTION

SPR220 i-Line photoresist is a general-purpose, multi-wavelength resist designed to cover a wide range of film thicknesses, 1–30 μm, with a single-coat process. SPR220 also has excellent adhesion and plating characteristics, which make it ideal for such thick film applications as MEMs and bump processes.

ADVANTAGES

- Broadband, g-Line and i-Line capable
- >10 μm film thickness in a single coat with good uniformity
- Fast photospeed: 210 mJ/cm² for 1.1 μm lines/spaces @ 4.0 μm film thickness (i-Line)
- Excellent wet and dry etch adhesion
- Au, Cu and Ni/Fe plating without cracking
- MIF and MIB developer compatible

See *Table 1* for recommended process conditions and *Figure 1* for various applications.

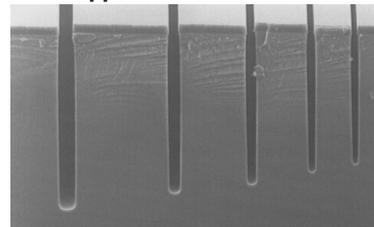
Table 1. Recommended Process Conditions		
	1.1–4.0 μm Thickness*	4.0–10.0 μm Thickness*
Thickness	1.1–4.0 μm	4.0–10.0 μm
Softbake	115°C/90 sec. Contact Hotplate	30 sec. step-down to 115°C/90 sec. Contact Hotplate**
Expose	ASML PAS 5500/200 i-Line (0.48 NA, 0.50σ)	
PEB	115°C/90 sec. Contact Hotplate	
Developer	MF™-24A @ 21°C, 60 sec. single spray puddle	

*Recommended for isolated spaces as well.

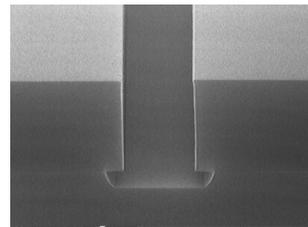
**Refer to softbake section for further details.

All data shown within this flyer used the process conditions listed above unless otherwise stated.

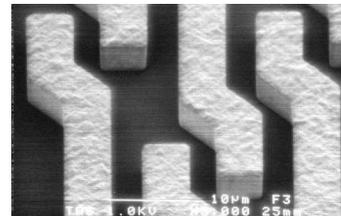
Figure 1. Various Applications



Etched Trenches (Bosh Process)
4–10 μm Features (up to 100 μm deep)



Wet Wafer Etch (1:5 HF 5 min.); 2 μm Feature



Gold Plated Deposit; 5 μm Features

Image courtesy of TriQuint

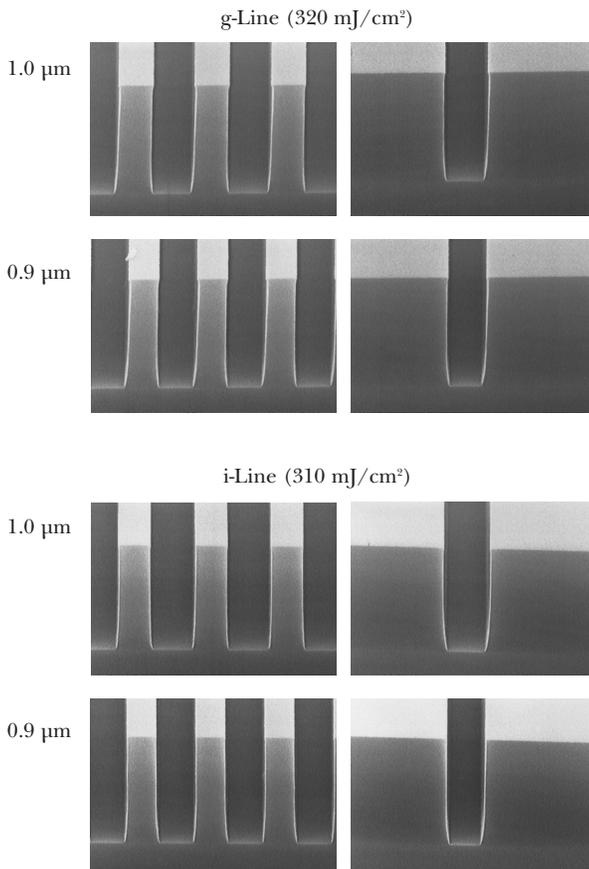
Table 2. Photospeed and Linearity of Dense Lines/Spaces at Various Thicknesses

	Film Thickness	Photospeed*	Linearity
g-Line	1.2 μm	210 mJ/cm ²	0.65 μm
g-Line	3.0 μm	320 mJ/cm ²	0.90 μm
g-Line	7.0 μm	470 mJ/cm ²	1.80 μm
i-Line	1.2 μm	160 mJ/cm ²	0.45 μm
i-Line	3.0 μm	310 mJ/cm ²	0.90 μm
i-Line	5.0 μm	380 mJ/cm ²	0.90 μm

*See Table 6 for recommended develop conditions.

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Figure 2. Resolution at 3.0 μm Film Thickness



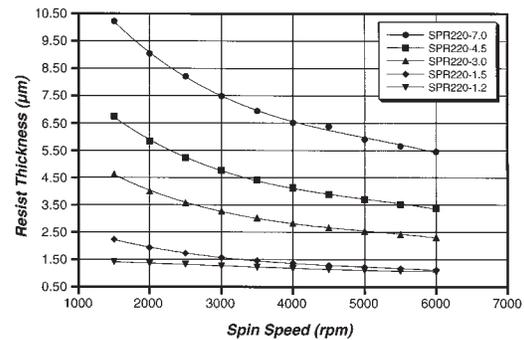
SUBSTRATE

SPR220 is compatible with a wide range of substrates, including but not limited to silicon, aluminum oxide, gold, copper and nickel-iron. A hexamethyldisilazane (HMDS)-based MICROPOSIT™ primer is recommended to promote adhesion with substrates that require such treatment. Vacuum vapor priming at 120°C for 30 seconds with concentrated HMDS is recommended.

COAT

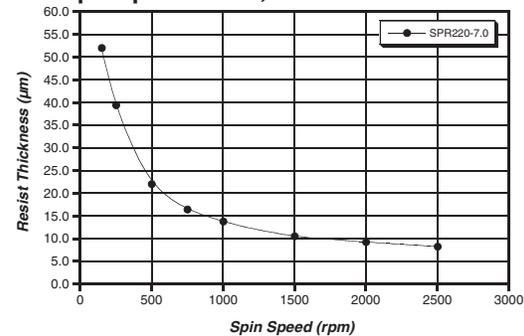
Figure 3 shows the relation between spin speed and resist thickness for 4-inch substrates. Figure 4 shows the relationship between spin speed and resist thickness for 8-inch (200 mm) substrates applying SPR220-7.0. Based on this curve a 375 RPM spin will yield a film thickness of approximately 30 μm . Nominal film thickness may vary slightly due to process, equipment and ambient conditions.

Figure 3. Spin Speed Curves on 4"



Coat Uniformity @ 7.31 μm , standard deviation = 0.036 μm , (33 points)

Figure 4. Spin Speed Curve, SPR220-7.0 on 8"



SOFTBAKE

The recommended softbake process for SPR220 for films up to 4.0 μm is 115°C for 90 seconds on a contact hotplate. For films greater than 4.0 μm , use a 30 second ramp in temperature (step-down to hotplate) to 115°C and hold for a minimum of 90 seconds. For film thickness greater than 12 μm , apply a 30 second ramp in temperature (step-down to hotplate) to 115°C and hold for a minimum of 300 seconds.

FILM THICKNESS MEASUREMENT

Figure 5 (see next page) shows the refractive index of SPR220 as a function of wavelength. Cauchy coefficients are listed in Table 3. Refractive index and dill parameters are listed in Table 4 and Table 5, respectively (see next page for these tables).

For film thickness greater than 12 μm the resist is exposed to an energy dose between 700 and 1,300 mJ/cm² (measured using standard radiometer @ 365 nm wavelength) using a high energy light source that generates peak output of wavelengths between 350 to 400 nm. Coating uniformity and the applied soft bake parameters can affect the required exposure energy needed for standardization and determination of the optimized exposure.

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Figure 5. Dispersion Curve

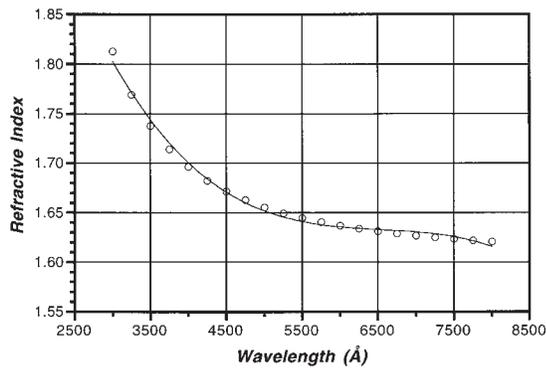


Table 3. Cauchy Coefficients

n_1	1.6035
n_2	$9.7122e+5$
n_3	$8.2082e+12$

Table 4. Refractive Index

RI @ 365 nm	0.73
RI @ 405 nm	1.30
RI @ 436 nm	1.67
RI @ 633 nm	1.63

Table 5. Dill Parameters

	365 nm	405 nm	436 nm
Dill A	0.5250	0.7075	0.4242
Dill B	0.0298	0.0173	0.0150

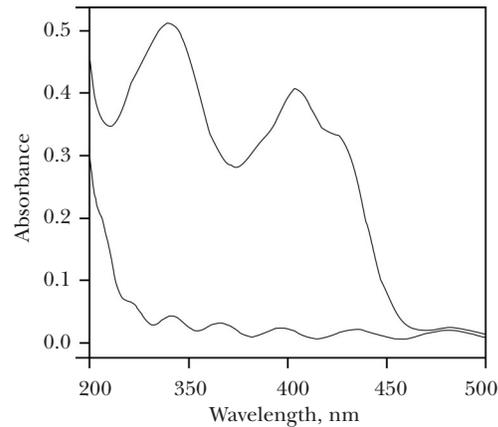
EXPOSE

The absorbance curves for the unexposed and exposed resist film are shown in *Figure 6*.

POST-EXPOSURE BAKE

Post-exposure bake (PEB) is run at the same temperature as the softbake. With thicker films (above 4 μm), a hold time is used between exposure and PEB to allow water (which is necessary to complete the photo-reaction) to diffuse back into the photoresist film. Thick films should use a minimum hold time of 35 minutes. For film thickness greater than 12 μm requires a minimum hold time of 120 minutes between exposure and develop should be applied.

Figure 6. Absorbance Curves



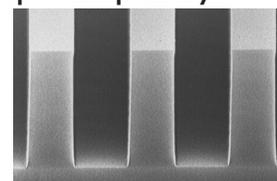
DEVELOP

SPR220 is optimized for 0.24N developers. Thicker films or high-throughput processes can utilize 0.26N developers. SPR220 has also been formulated for use in metal-ion free and metal-ion bearing developers, as demonstrated in *Figure 7*. See *Table 6* for recommended develop conditions.

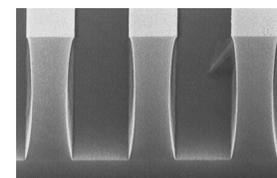
Table 6. Recommended Develop Conditions

	1.2 μm FT	3.0 μm FT	5.0 μm FT	7.0 μm FT
MF-24A	40 sec. SP	60 sec. SP	60/60 sec. DP	60/60 sec. DP
MF-26A	40 sec. SP	60 sec. SP	80 sec. SP	60/60 sec. DP
M452	—	3 min. Imm.	3 min. Imm.	3 min. Imm.
M453	—	—	3 min. Imm.	3 min. Imm.

Figure 7. Developer Compatibility



MIF (MF-24A)



MIB (M452)

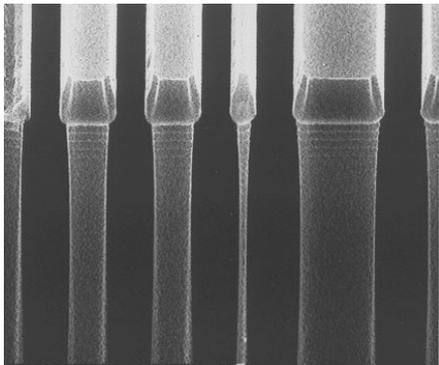
For thick film application 12 μm or greater using MF-26A developer, the overall development time will behave similar to the thin film time cited in the table *Figure 7* above.

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ETCH RESISTANCE

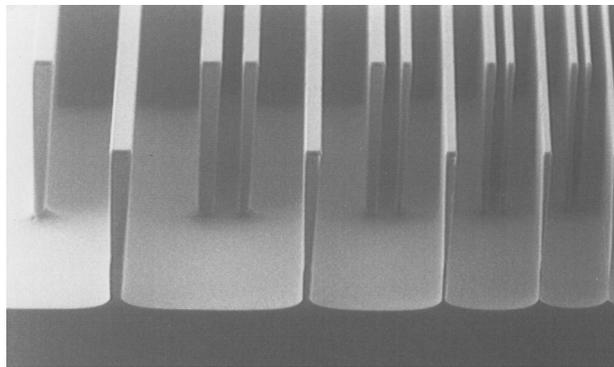
Figure 8 shows the etch performance of SPR220 with a Bosch Etch process (100:1 etch selectivity).

Figure 8. Etch Performance



Etched Lines (Bosch Process)
2.5 to 10 μm Features (up to 200 μm deep)

Etched Lines



5 to 20 μm Features (up to 100 μm deep)

PHOTORESIST REMOVAL

SPR220 can be removed with MICROPOSIT REMOVER 1165. A two-bath process is recommended with each bath at a temperature of 80°C (176°F). The first bath removes the bulk of the photoresist and the second removes residual traces of photoresist. Please consult specific remover data sheets for additional process information.

HANDLING PRECAUTIONS

CAUTION! SPR220 is a combustible liquid containing ethyl lactate, anisole and n-amyl acetate. Handle with care. Ground and bond all containers when handling or transferring combustible materials. Contact with eyes, skin and mucous membranes can cause irritation. In case of eye or skin contact, flush affected areas with plenty of water for at least 15 minutes. If irritation persists, contact your physician immediately. Avoid breathing vapors or mists. Use with adequate ventilation. It is highly recommended that during handling chemical goggles, chemical gloves and protective clothing be worn.

Please consult the Material Safety Data Sheet prior to use.

WASTE TREATMENT

SPR220 contains ethyl lactate, anisole and n-amyl acetate and may be included with other wastes containing similar organic solvents to be discarded for destruction or reclaim in accordance with local, state, and federal regulations.

It is your responsibility to ensure the disposal of SPR220 and residues therefrom is made in compliance with all applicable environmental regulation.

STORAGE

Recommended storage for SPR220 is in an upright position in a dry area at 40–60°F (4–15°F). Keep away from oxidizers, acids, and bases. Keep container sealed when not in use.

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UNITED STATES

Marlborough, MA

Tel: 800.832.6200

Fax: 508.485.9113

JAPAN

Tokyo

Tel: +81.3.5213.2910

Fax: +81.3.5213.2911

ASIA

Hong Kong

Tel: +852.2680.6888

Fax: +852.2680.6333

EUROPE

Paris, France

Tel: +33.1.40.02.54.00

Fax: +33.1.40.02.54.07

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